IXTQ75N10P-OSEN

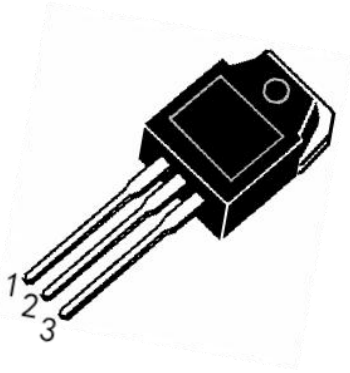
LOW Voltage N-Channel MOSFET

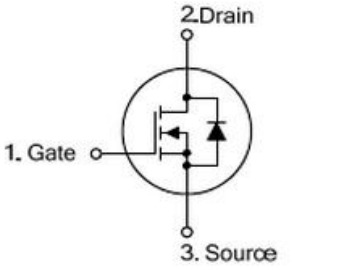
◆ Features：

- ✧ Fast switching speed
  开关速度快
- ✧ Low gate charge
  低门充电
- ✧ High power and current handing capability
  高功率和电流处理能力
- ✧ RoHS compliant
  符合 RoHS 标准

RoHS COMPLIANT

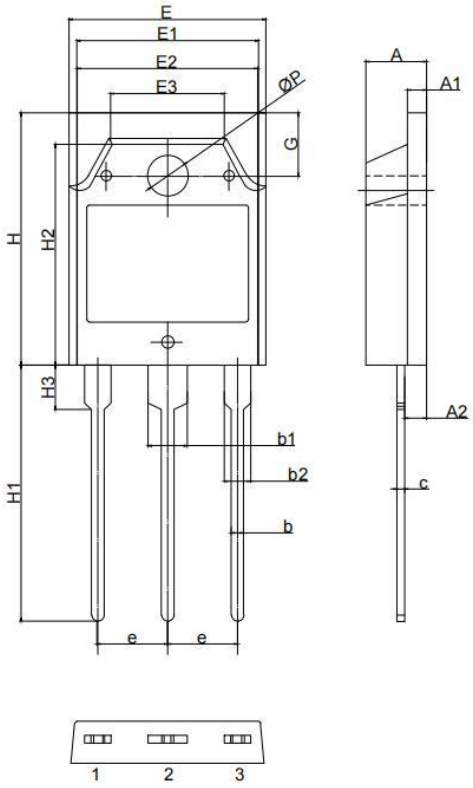
TO-3PNB





◆ Applications

- ✧ DC to DC converters
  直流到直流转换
- ✧ Synchronous Rectification
  同步整流



TO-3PNB尺寸表/mm			
Symbol	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.30	1.50	1.60
A2	1.40	1.50	1.60
b	0.80	1.00	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.20	15.60	16.00
E1	13.20	13.40	13.60
E2	13.10	13.50	13.50
E3	9.10	9.30	9.50
H	19.80	20.00	20.20
H1	20.10	20.30	20.50
H2	18.50	18.70	18.90
H3	3.20	3.50	3.80
G	4.80	5.00	5.20
ØP	3.00	3.20	3.40

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V_{DSS}	Drain-Source Voltage 漏源电压	**100**	V
V_{GS}	Gate-Source Voltage-Continuous 栅源电压	**±20**	V
I_D	Drain Current-Continuous（Note 2） 漏极持续电流	**75**	A
I_{DM}	Drain Current-Single Plused（Note 1） 漏极单次脉冲电流	**200**	A
P_D	Power Dissipation （Note 2） 功率损耗	**360**	W
T_j	Max.Operating junction temperature 最大结温	**150**	℃

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B_{VDSS}	Drain-Source Breakdown Voltage Current （Note 1） 漏极击穿电压	**100**	--	--	V	I_D=250μA，V_{GS}=0V
$V_{GS(th)}$	Gate Threshold Voltage 栅极开启电压	**2.0**	--	**4.0**	V	V_{DS}=V_{GS}，I_D=250μA
$R_{DS(on)}$	Drain-Source On-Resistance 漏源导通电阻	--	**21**	**25**	mΩ	V_{GS}=10V，I_D=37A
I_{GSS}	Gate-Body Leakage Current 栅极漏电流	--	--	**±100**	nA	V_{GS}=±20V，V_{DS}=0
I_{DSS}	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	**1**	μA	V_{DS}=100V，V_{GS}=0
gfs	Forward Trans conductance 正向跨导	--	**28**	--	S	V_{DS}=10V，I_D=37A

Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time 开启延迟时间	--	**29**	--	ns	V_{DD}=50V, I_D=37.5A， R_G=10Ω
T_r	Rise Time 上升时间	--	**56**	--	ns	
$T_{d(off)}$	Turn-Off Delay Time 关闭延迟时间	--	**69**	--	ns	
T_f	Fall Time 下降时间	--	**50**	--	ns	
Q_g	Total Gate Charge 栅极总电荷	--	**77**	--	nC	V_{DS}=50V， V_{GS}=10V， I_D=37.5A
Q_{gs}	Gate-Source Charge 栅源极电荷	--	**20**	--	nC	
Q_{gd}	Gate-Drain Charge 栅漏极电荷	--	**43**	--	nC	
Dynamic Characteristics						
C_{iss}	Input Capacitance 输入电容	--	**3600**	--	pF	V_{DS}=25V，V_{GS}=0， f=1MHz
C_{oss}	Output Capacitance 输出电容	--	**780**	--	pF	
C_{rss}	Reverse Transfer Capacitance 反向传输电容	--	**350**	--	pF	
I_S	Continuous Drain-Source Diode Forward Current（Note 2） 二极管导通正向持续电流	--	--	**75**	A	
V_{SD}	Diode Forward On-Voltage 二极管正向导通电压	--	--	**1.3**	V	I_S=30A，V_{GS}=0
$R_{th(j-c)}$	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	**0.35**	°C/W	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature
Note 2: Pulse test: PW <= 300us , duty cycle <= 2%.

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